

# MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV

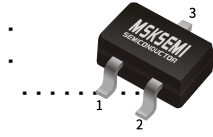


GDT



PLED

Product data sheet



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

GH1&''

TRANSISTOR (NPN)

95H F9G

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)

7 @ GG= 75HCB'C: hFE%

F U b _	67, %!%'	67, %!&'	67, %!( \$'
F U b [ Y'	%%\$!&)' \$'	% \$!( \$\$'	&)' \$!* \$\$'
A U _]b[ '	* 5'	* 6'	* 7'

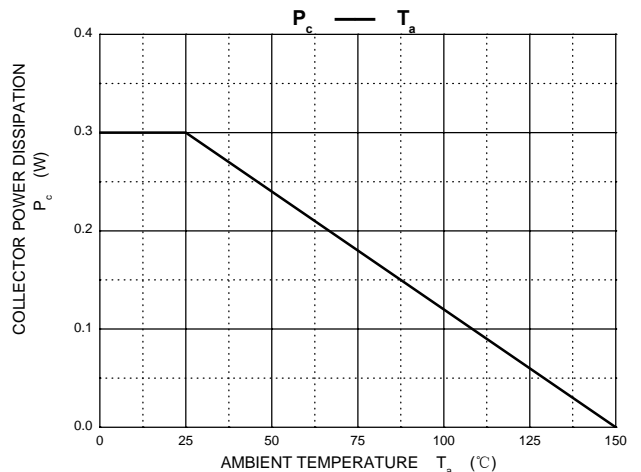
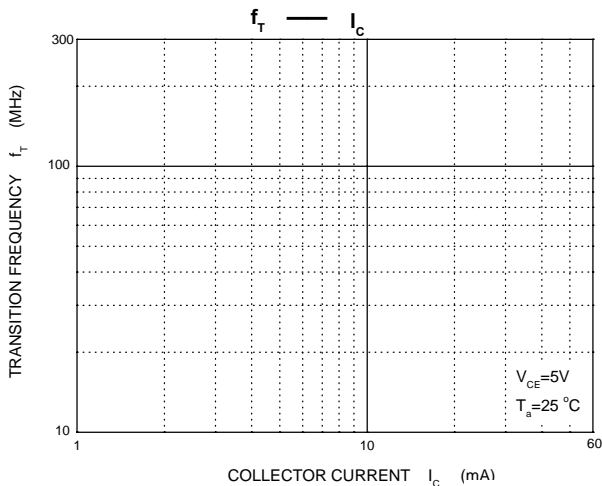
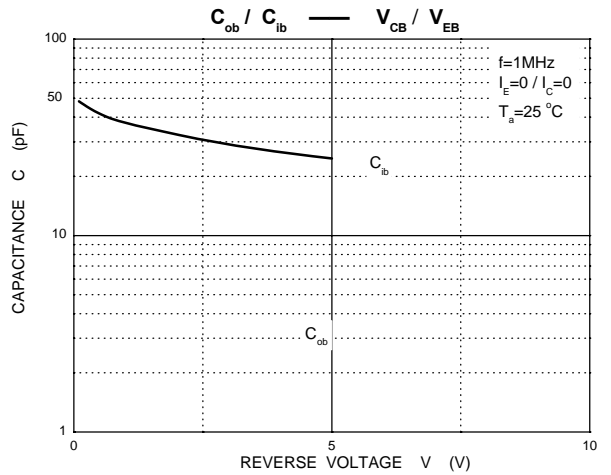
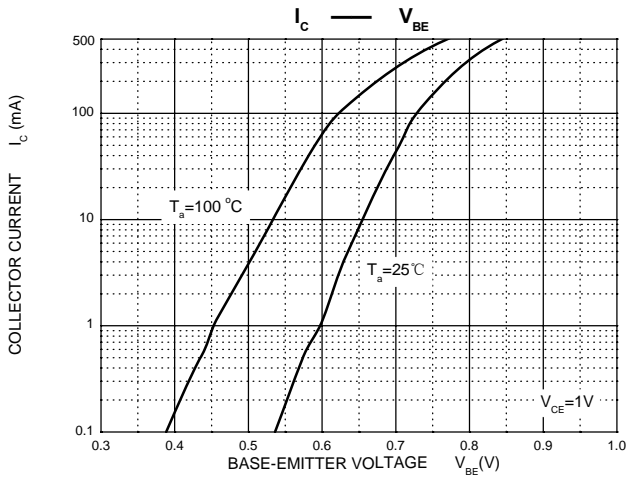
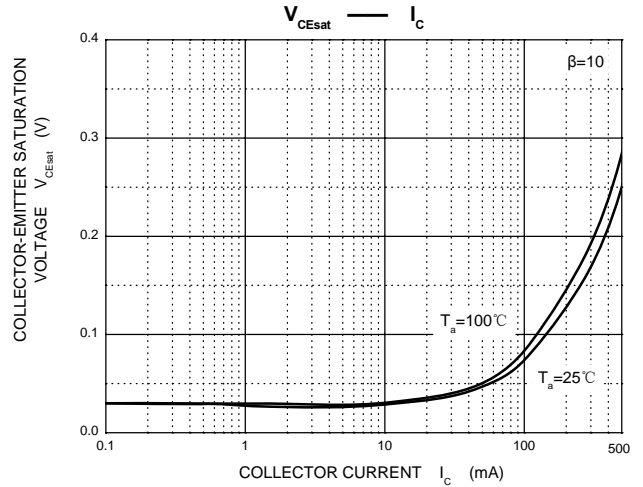
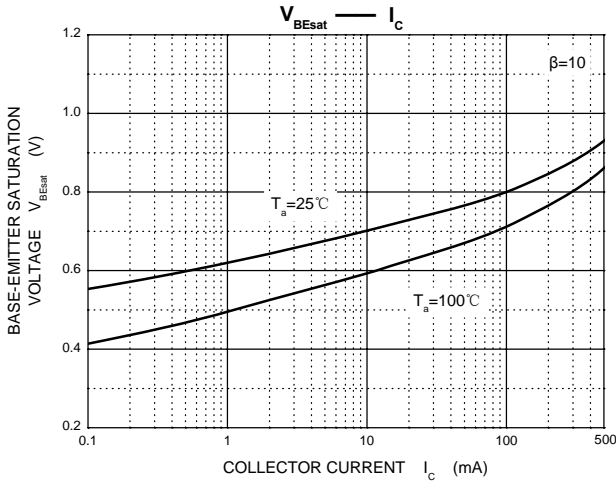
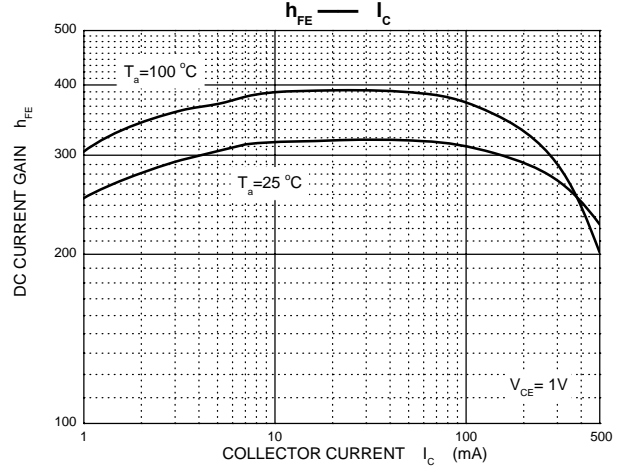
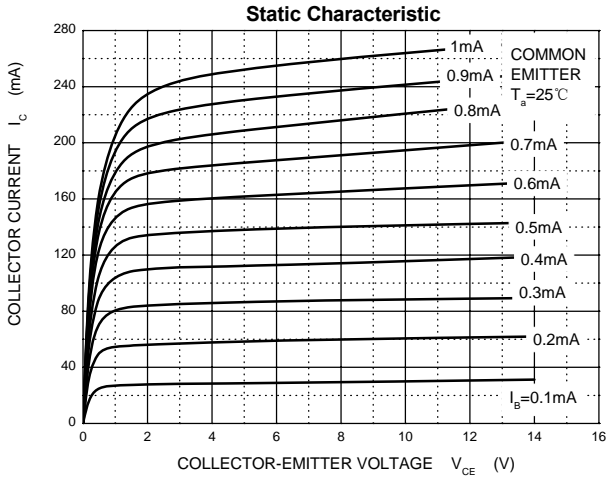
MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	500	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	417	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

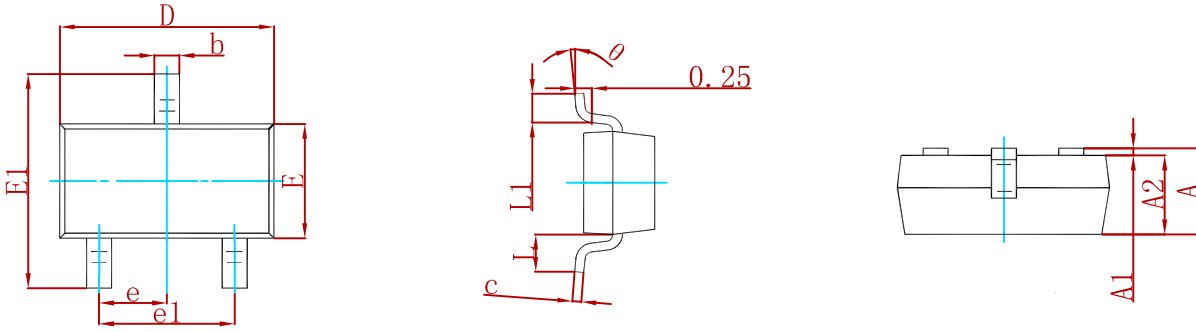
9 @ 7 HF 7 5 @ 7 < 5 F 5 7 H 9 F -GH 7 G'fh 1 &) °C i b`Ygg'cH Yfk jgY gdYWZ YXL

Symbol	Parameter	Value	Typ	Aax	Unit
V <sub>CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> =0	50			V
V <sub>CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	45			V
V <sub>EBO</sub>	I <sub>E</sub> = 1μA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	V <sub>CB</sub> = 45 V, I <sub>E</sub> =0			0.1	μA
I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> =0			0.1	μA
h <sub>FE(1)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 100mA	100		600	
h <sub>FE(2)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 500mA	40			
V <sub>CE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			0.7	V
V <sub>BE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			1.2	V
V <sub>BE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 500mA			1.2	V
C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		10		pF
f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10mA f=100MHz	100			MHz

Typical Characteristics

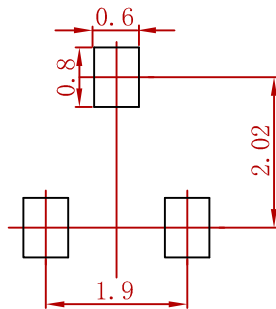


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Suggested Pad Layout**



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance: ± 0.05mm.
  3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
BC817-16/25/40	SOT-23	3000

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